(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
15 September 2005 (15.09.2005)

PCT

(10) International Publication Number
WO 2005/084225 A2

(51) International Patent Classification: Not classified

(21) International Application Number:
PCT/US2005/006058

(22) International Filing Date: 25 February 2005 (25.02.2005)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10/789,638 27 February 2004 (27.02.2004) US

(71) Applicant *(for all designated States except US)*: SOLAICX, INC. [US/US]; Solaicx, Inc., 5102 Calle del Sol, Santa Clara, CA 95054, CA 95054 (US).

(72) Inventor: BENDER, David, L.; 2212 Rustic Park Court, Thousand Oaks, CA 91362 (US).

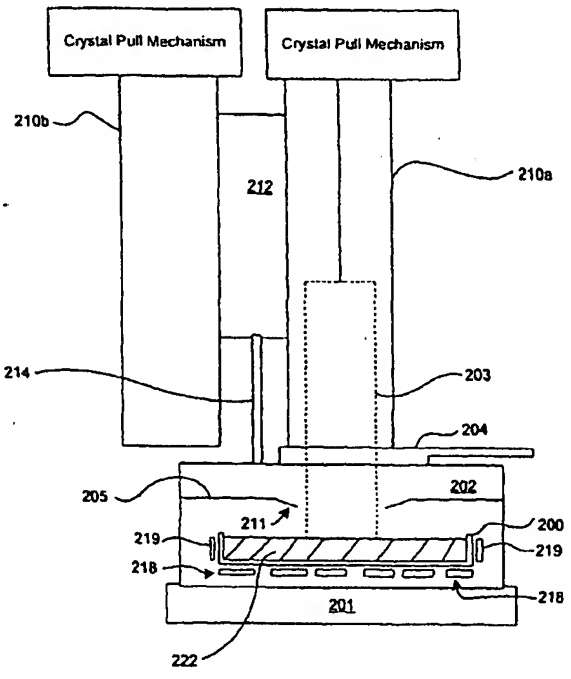
(74) Agent: HETHERINGTON, Michael; Mr. Michael Hetherington, P. O. Box 61047, Palo Alto, CA 94306 (US).

(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO,

[Continued on next page]

(54) Title: SYSTEM FOR CONTINUOUS GROWING OF MONOCRYSTALLINE SILICON



Low Aspect Ratio Crucible

(57) Abstract: An improved system based on the Czochralski process for continuous growth of a single crystal ingot comprises a low aspect ratio, large diameter, and substantially flat crucible, including an optional weir surrounding the crystal. The low aspect ratio crucible substantially eliminates convection currents and reduces oxygen content in a finished single crystal silicon ingot. A separate level controlled silicon pre-melting chamber provides a continuous source of molten silicon to the growth crucible advantageously eliminating the need for vertical travel and a crucible raising system during the crystal pulling process. A plurality of heaters beneath the crucible establish corresponding thermal zones across the melt. Thermal output of the heaters is individually controlled for providing an optimal thermal distribution across the melt and at the crystal / melt interface for improved crystal growth. Multiple crystal pulling chambers are provided for continuous processing and high throughput.

WO 2005/084225 A2

SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Declaration under Rule 4.17:

— *as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii)) for the following designations AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SM, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW, ARIPO patent (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian patent (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI patent (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG)*

Published:

— *without international search report and to be republished upon receipt of that report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.